

RJK0855DPB

80V, 30A, 11 m Ω max. Silicon N Channel Power MOS FET Power Switching

R07DS1056EJ0200 (Previous: REJ03G1884-0100)

Rev.2.00

Apr 11, 2013

Features

- High speed switching
- Low drive current
- Low on-resistance $R_{DS(on)} = 8.2 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V)}$
- Pb-free
- Halogen-free
- High density mounting

Outline

RENESAS Package code: PTZZ0005DA-A (Package name: LFPAK)

1, 2, 3 Source
4 Gate
5 Drain

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	80	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I _D	30	А
Drain peak current	I _{D(pulse)} Note1	120	А
Body-drain diode reverse drain current	I _{DR}	30	А
Avalanche current	I _{AP} Note 2	30	А
Avalanche energy	E _{AS} Note 2	12	mJ
Channel dissipation	Pch Note3	60	W
Channel to Case Thermal Resistance	θch-C	2.08	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at L=10uH, Tch = 25°C, Rg \geq 50 Ω
- 3. Tc = 25°C

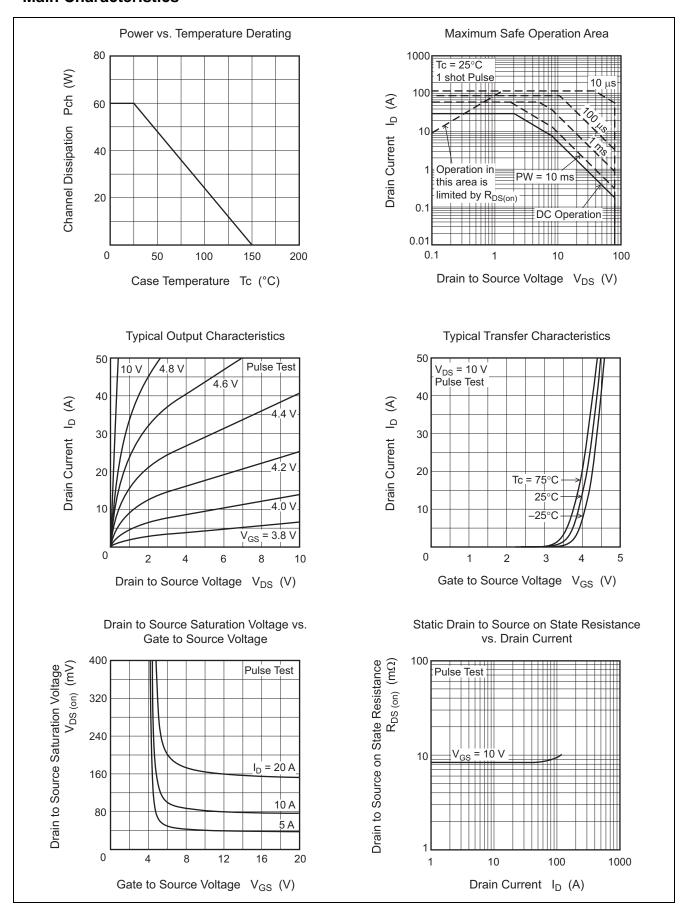
Electrical Characteristics

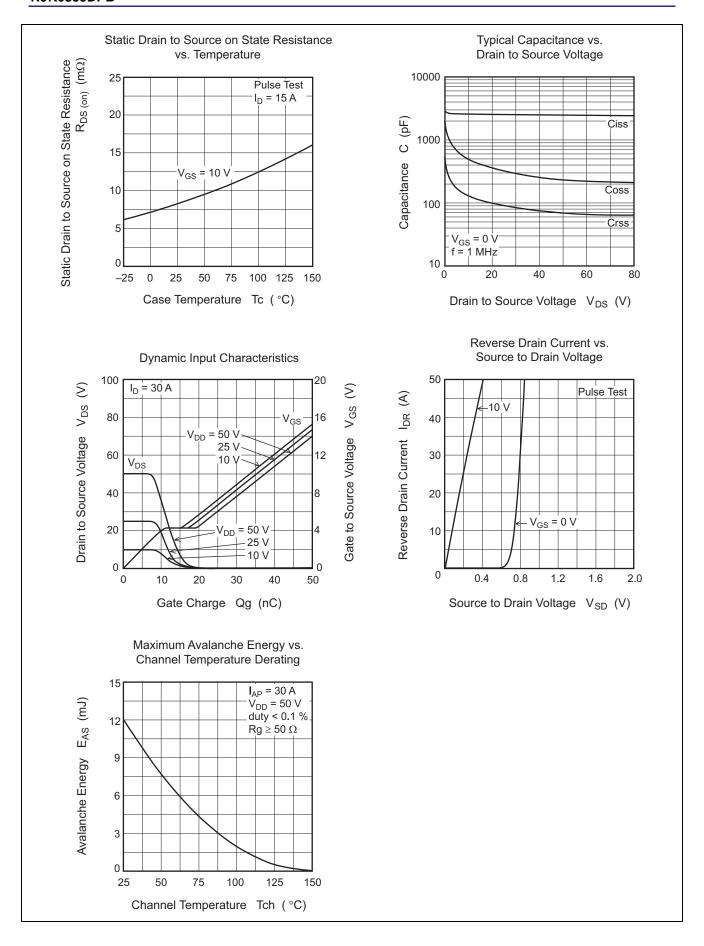
 $(Ta = 25^{\circ}C)$

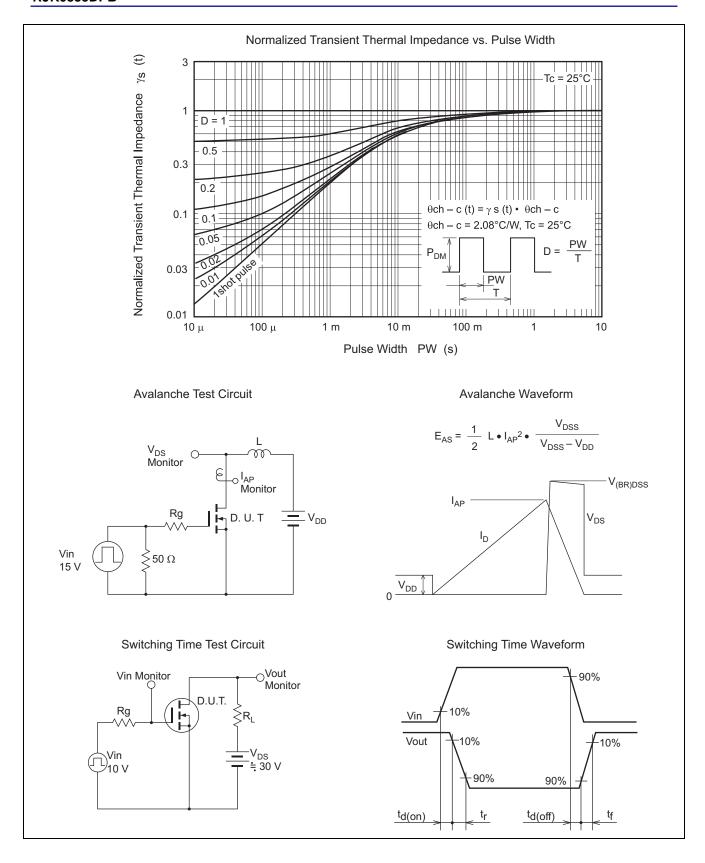
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	80	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate to source leak current	I _{GSS}			±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	8.2	11	mΩ	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	_	42	_	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2550	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	500	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	130	_	pF	
Gate Resistance	Rg	_	0.5	_	Ω	
Total gate charge	Qg	_	35	_	nC	$V_{DD} = 25 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} = 30 \text{ A}$
Gate to source charge	Qgs	_	11	_	nC	
Gate to drain charge	Qgd	_	6.5	_	nC	
Turn-on delay time	t _{d(on)}	_	14	_	ns	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A},$
Rise time	t _r	_	6.4	_	ns	$V_{DD} \cong 30 \text{ V, } R_L = 2 \Omega,$ $Rg = 4.7 \Omega$
Turn-off delay time	t _{d(off)}	_	34	_	ns	
Fall time	t _f	_	8.0	_	ns	
Body-drain diode forward voltage	V_{DF}	_	0.8	1.1	V	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}^{Note4}$
Body-drain diode reverse recovery time	t _{rr}	_	44	_	ns	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}$
						di _F / dt = 100 A/ μs

Notes: 4. Pulse test

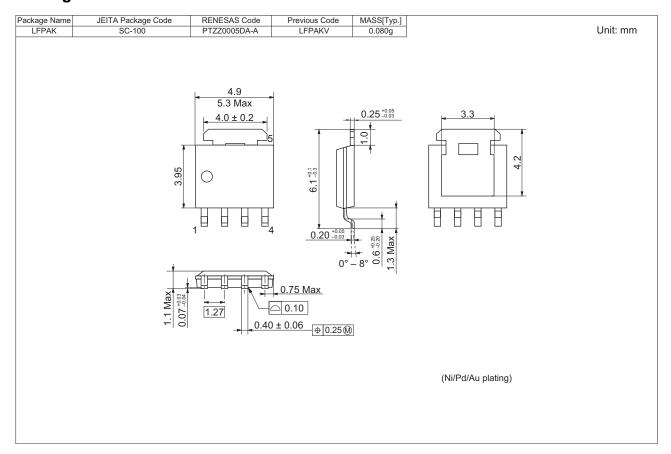
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK0855DPB-00-J5	2500 pcs	Taping

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